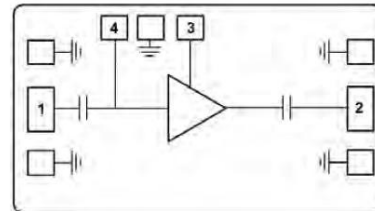


Features

- Two operating mode: high power consumption and low power consumption
- Frequency: 0.8-18GHz
- Noise Figure: 1.9dB@65mA, 1.7dB@40mA
- Gain: 16.5dB@65mA, 15.5dB@40mA
- P1dB: 18dBm@65mA, 17.5dBm@40mA
- Psat: 19.5dBm@65mA, 19dBm@40mA
- Power Supply: +5V@65mA, VG is floating
- +5V@40mA, VG connected to GND
- Input/Output: 50Ω
- Die Size: 1.5 x 1.0 x 0.1 mm

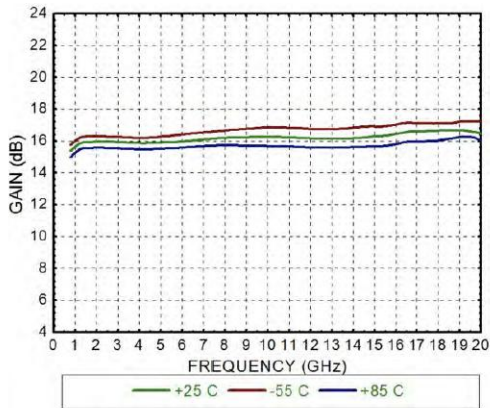
Functional Block Diagram

Typical Applications

- Test Instrumentation
- Microwave Radio & VSAT
- Military & Space
- Telecom Infrastructure
- Fiber Optics

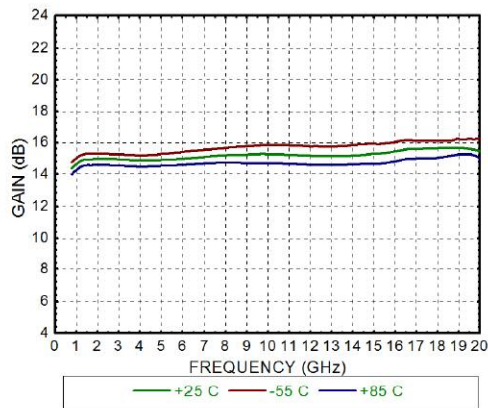
Electrical Specifications
TA = +25°C, VDD=+5V

| Parameters | VG is floating | | | VG connected to GND | | | Units |
|--------------------------------------|----------------|-------------|-----------|---------------------|-------------|-----------|------------|
| | Min. | Typ. | Max. | Min. | Typ. | Max. | |
| Frequency | 0.8-18 | | | 0.8-18 | | | GHz |
| Gain | | 16.5 | | | 15.5 | | dB |
| Gain Flatness | | ±0.5 | | | ±0.3 | | dB |
| Input Return Loss | | 10 | | | 10 | | dB |
| Output Return Loss | | 12 | | | 12 | | dB |
| Output 1dB Compression (P1dB) | | 18 | | | 17.5 | | dBm |
| Psat | | 19.5 | | | 19 | | dBm |
| Noise Figure | | 1.9 | | | 1.7 | | dB |
| Operating current | 45 | 65 | 85 | 25 | 40 | 60 | mA |

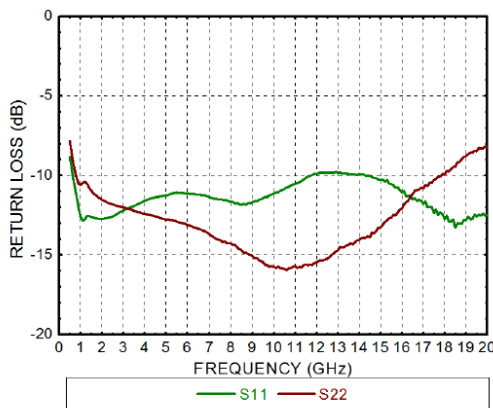
Gain (VG is floating)



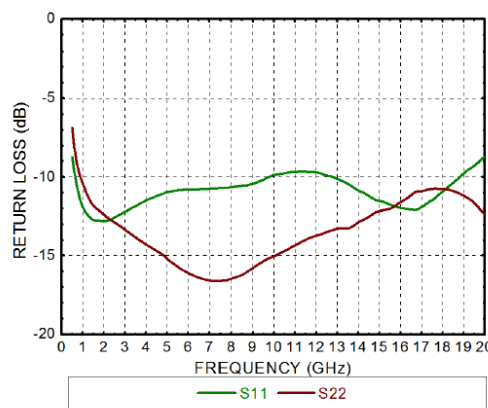
Gain(VG connected to GND)



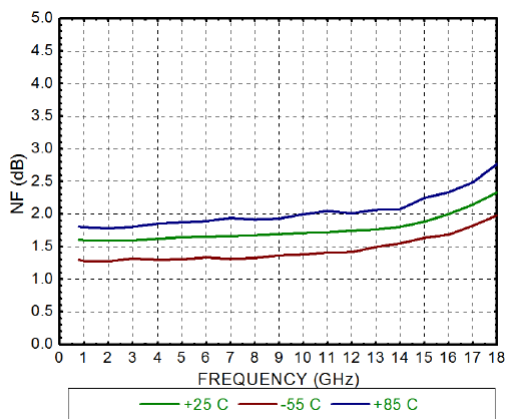
Return Loss(VG is floating)



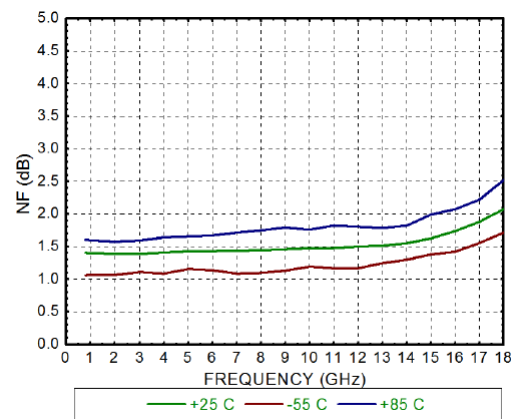
Return Loss(VG connected to GND)



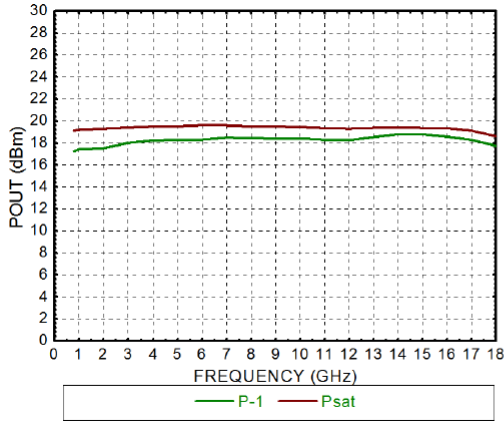
Noise Figure (VG is floating)



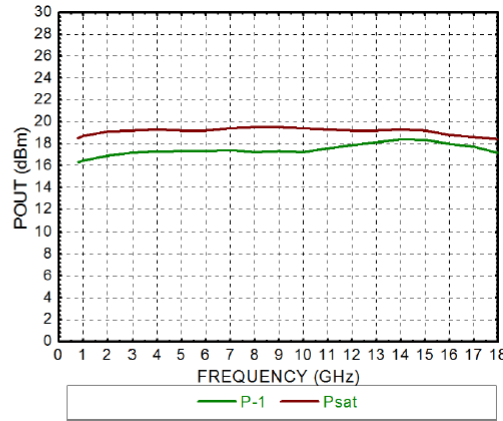
Noise Figure(VG connected to GND)



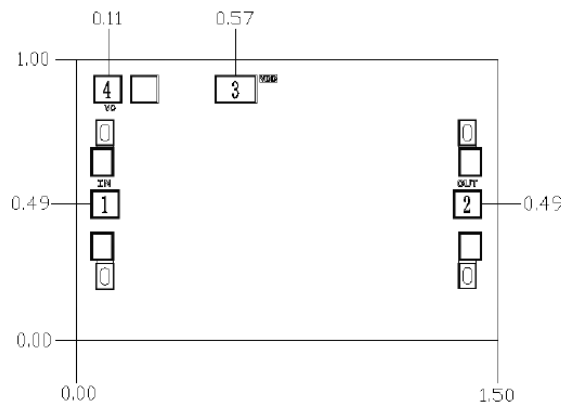
Pout(VG is floating)



Pout(VG connected to GND)



Outline Drawing:
All Dimensions in mm

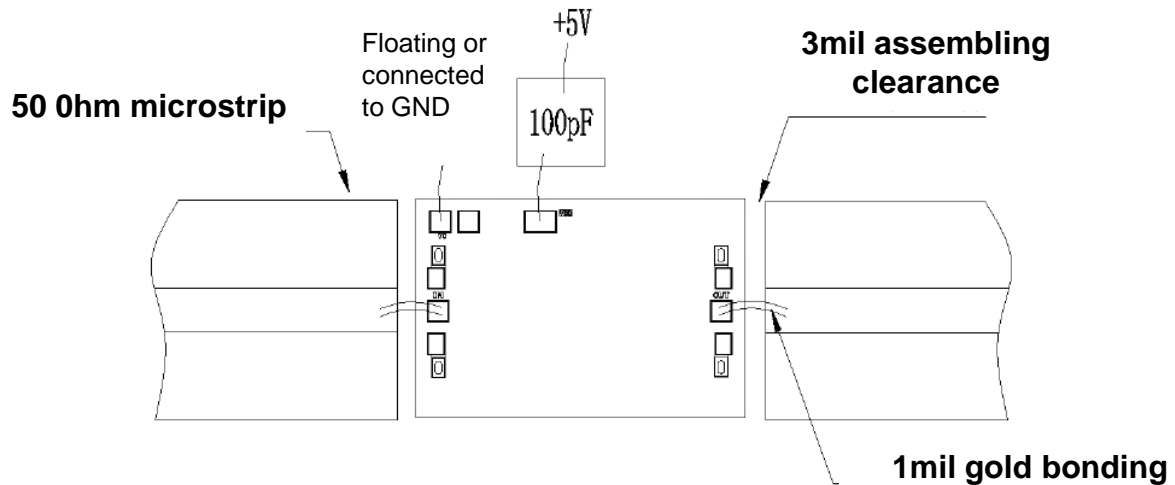


Pad Description

| PAD | Function | Description |
|------------|----------|---|
| 1 | IN | This pad is AC coupling, 50 ohm matched. |
| 2 | OUT | This pad is AC coupling, 50 ohm matched. |
| 3 | VDD | This pad provides power supply for the amplifier. It should be connected to extra 100pF bypass capacitor. |
| 4 | VC | This pad determines the die's operating mode. It could be floating or connected to GND. |
| Die Bottom | GND | Die backside must connect to RF/DC GND. |



Assembly Drawing



Notes:

1. Die thickness: 100um
2. Typical bond pad is 100*100 μm^2
3. Bond pad metalization: Gold
4. Backside metalization: Gold
5. Backside of the die (GND)
6. No connection required for unlabeled bond pads

Maximum Ratings:

1. Maximum drain voltage: +7V
2. Maximum input power: +18dBm
3. Operating temperature: -55°C to +85°C
4. Storage temperature: -65°C to +150°C